

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

3N247-M SERIES
3N254-M SERIES

SILICON BRIDGE RECTIFIER

CASE B-M

DESCRIPTION

The CENTRAL SEMICONDUCTOR 3N247-M, 3N254-M series types are silicon single phase full wave bridge rectifiers designed for general purpose applications.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

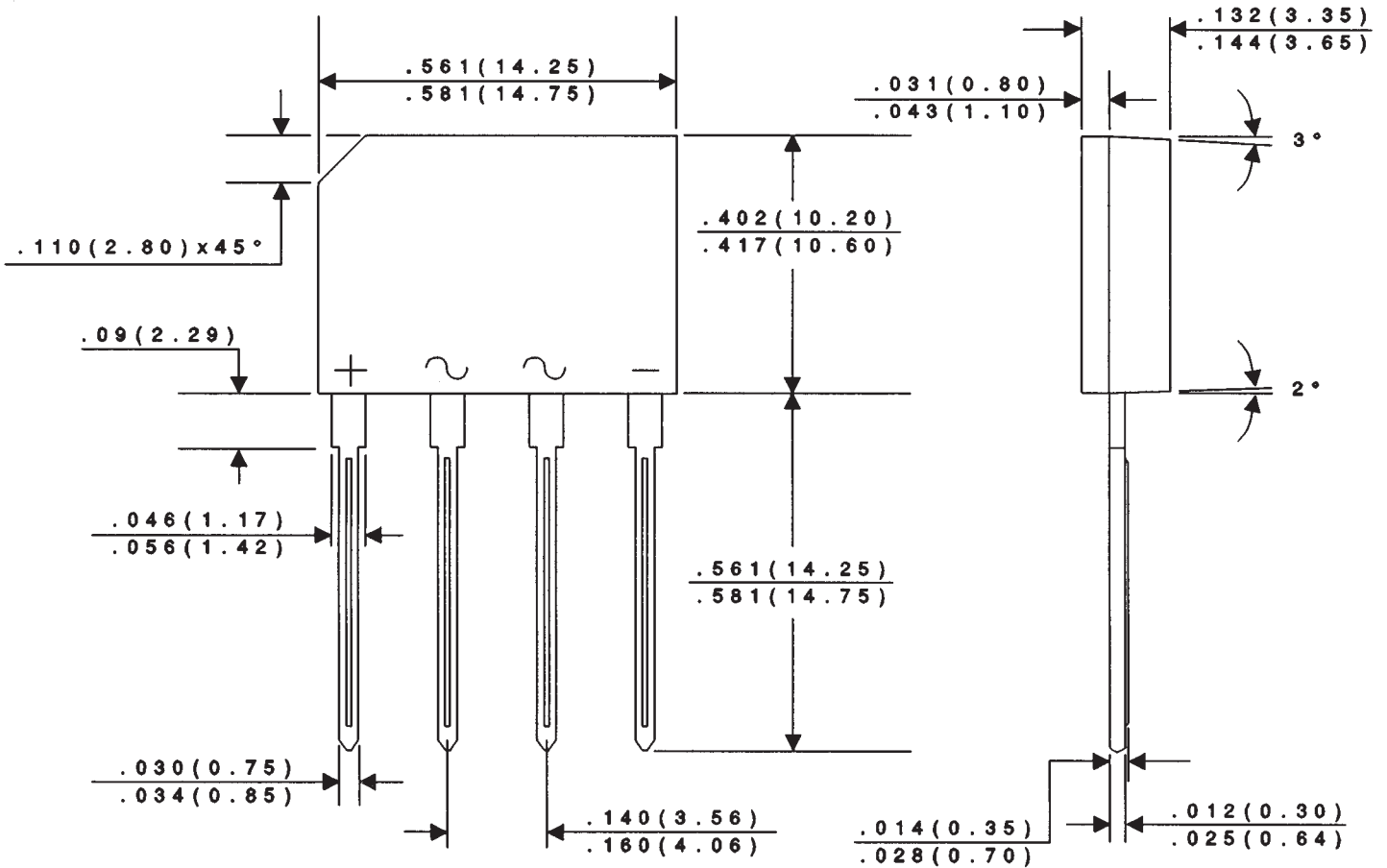
	SYMBOL	3N	3N	3N	3N	3N	3N	UNITS
		<u>247-M</u>	<u>248-M</u>	<u>249-M</u>	<u>250-M</u>	<u>251-M</u>	<u>252-M</u>	
		3N	3N	3N	3N	3N	3N	
		<u>254-M</u>	<u>255-M</u>	<u>256-M</u>	<u>257-M</u>	<u>258-M</u>	<u>259-M</u>	
Peak Repetitive Reverse Voltage	V _{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V _R	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	70	140	280	420	560	700	V
Average Forward Current (3N247-M Series @ T _A =75°C)	I _O			1.5				A
Average Forward Current (3N254-M Series @ T _A =55°C)	I _O			2.0				A
Peak Forward Surge Current (3N247-M Series)	I _{FSM}				30			A
Peak Forward Surge Current (3N254-M Series)	I _{FSM}				55			A
Operating and Storage Junction Temperature	T _J , T _{stg}			-65 to +150				°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V _F	I _F =3.14A (3N247-M Series)		1.3	V
V _F	I _F =3.14A (3N254-M Series)		1.1	V
I _R	V _R =Rated V _{RRM}		10	μA

(OVER)

CASE B-M - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.